2SA1006,1006A,1006B/2SC2336,2336A,2336B

PNP/NPNエピタキシアル形 シリコントランジスタ(EBT) 低周波電力増幅, 高周波電力増幅用 PNP/NPN Silicon Epitaxial Transistor(EBT)

Audio Frequency Power Amplifier

High Frequency Power Amplifier

- ○実効出力150~500 W高級ステレオパワーアンプのドライバ段として最適。
- ○高耐圧である。→ V_{CEO}=180 V, 200 V, 250 V
- ○安全動作領域が広い。
- Of_Tが高い。→80/95 MHz TYP.
- Ohfeリニアリティが良く、コンプリメンタリ性も良い。

絶対最大定格/ABSOLUTE MAXIMUM RATINGS (Ta=25 ℃)

| | 項 | 目 | | 略号 | 2SA1006 | 2SA1006A | 2SA1006B | 2SC2336 | 2SC2336A | 2SC2336B | 単位 |
|----|-------|------|-----|--------------------------|---------|-----------------|----------|---------|----------|----------|------|
| コレ | クタ・ベ | ース間 | 電圧 | V _{CBO} | -180 | - 200 | -250 | 180 | 200 | 250 | V |
| コレ | クタ・エミ | ッタ間 | 電圧 | V _{CEO} | -180 | -200 | -250 | 180 | 200 | 250 | V |
| エミ | ッタ・ベ | ース間 | 電圧 | V _{EBO} | | -5.0 | - | | 5.0 | | V |
| コレ | クタ電 | 流(直 | 流) | I _{C(DC)} | | -1.5 | | | 1.5 | | A |
| コレ | クタ電 | 流 (パ | ルス) | I _{C(pulse)} * | | -3.0 | | | 3.0 | | A |
| 全 | 損 | | 失 | P _{T(Ta=25 °C)} | | 1.5 | | | 1.5 | | W |
| 全 | 損 | | 失 | P _{T(Te=25 ·C)} | | 25 | | | 25 | | W |
| ジャ | ンクシ | ョン | 温度 | T, | | 150 | | | 150 | | °C , |
| 保 | 存 | 温 | 度 | Tstg | | $-55 \sim +150$ | | **· | -55~+150 | | °C |

^{*} PW \leq 10 ms, duty cycle \leq 50 %

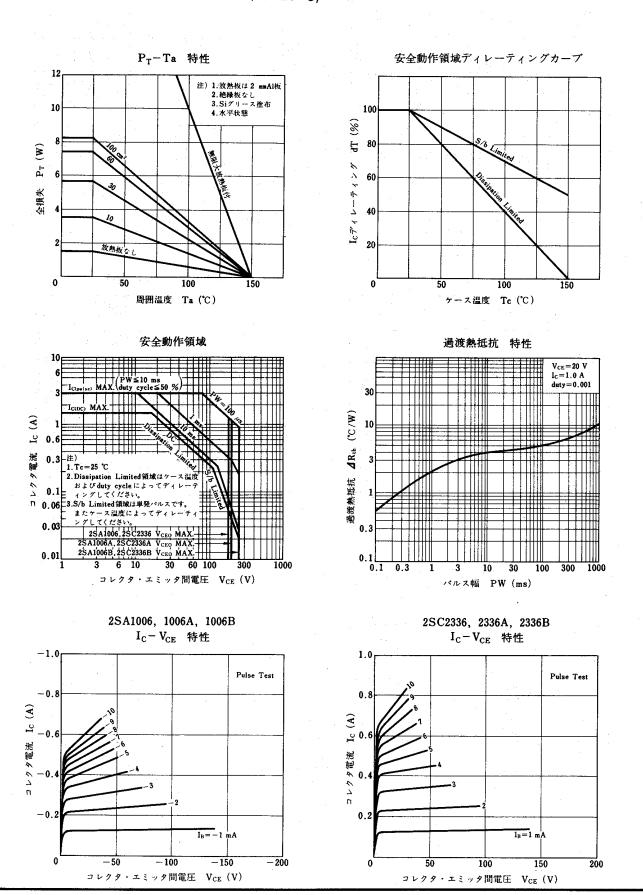
電気的特性 / ELECTRICAL CHARACTERISTICS (Ta=25 ℃) 2SA1006,1006A,1006B/2SC2336,2336A,2336B

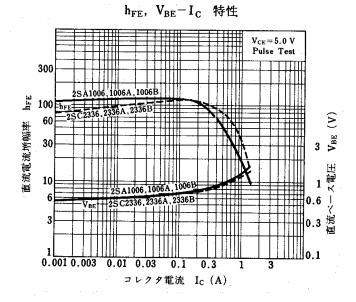
| 項目 | 略号 | 条件 | | MIN. | TYP. | MAX. | 単位 |
|-------------|----------------------|--|---|------|----------|----------|-----|
| コレクタしゃ断電流 | I _{CBO} | $V_{CB} = -150/150 \text{ V}, I_E = 0$ | | | | -1.0/1.0 | μA |
| エミッタしゃ断電流 | I _{EBO} | $V_{EB} = -3.0/3.0 \text{ V}, I_{C} = 0$ | | | | -1.0/1.0 | μА |
| 直流電流増幅率 | h _{FE1} | $V_{CE} = -5.0/5.0 \text{ V}, I_{C} = -5.0/5.0 \text{ mA}$ | * | 30 | 120/90 | | : |
| 直流電流増幅率 | h _{FE2} | $V_{CE} = -5.0/5.0 \text{ V}, I_{C} = -150/150 \text{ mA}$ | * | 60 | 120 | 320 | |
| コレクタ飽和電・圧 | V _{CE(sat)} | $I_C = -500/500 \text{ mA}, I_B = -50/50 \text{ mA}$ | * | | -0.4/0.3 | -1.0/1.0 | V |
| ベース飽和電圧 | V _{BE(sat)} | $I_C = -500/500 \text{ mA}, I_B = -50/50 \text{ mA}$ | * | 7 | -1.0/1.0 | -1.5/1.5 | V |
| 利 得 帯 域 幅 積 | f _T | $V_{CE} = -10/10 \text{ V}, I_{C} = -100/100 \text{ mA}$ | | | 80/95 | | MHz |
| コレクタ容量 | Сов | $V_{CB} = -10/10 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$ | | | 45/30 | | pF |

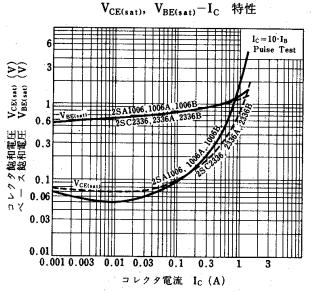
^{*} Pulse Test / PW \leq 350 μ s, duty cycle \leq 2 %

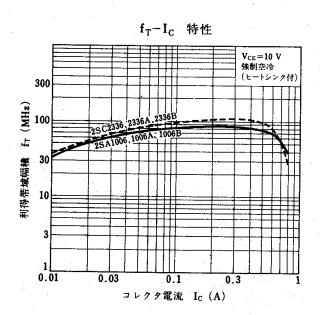
hFE2 区分/R:60~120 Q:100~200 P:160~320

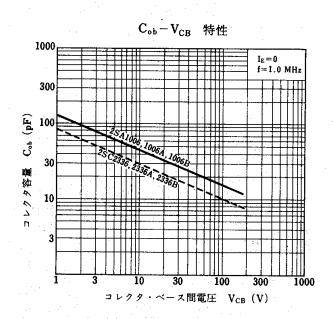
特性曲線/TYPICAL CHARACTERISTICS(Ta=25°C)



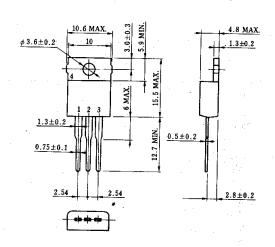








外形図/PACKAGE DIMENSIONS (Unit:mm)



電極接続

- 1. Base
- 2. Collector(Fin)
- 3. Emitter
- 4. Fin

Transistors L

• Darlington Power Transistors

| V _{CEO} [V] | Package | 1.5 | 2.0 | 3.0 | 5.0 | 7.0 | 10 | 15 | 25 |
|----------------------|----------|-----|------------------|-----|-----------------------------|-----|---|--|--------------------|
| 60 | TO-126 | | NTD985 NTB794 | | | | | | |
| .80 | TO-126 | | NTD986 NTB795 | | | | NTD411 (TO-3) | | |
| 100 | TO-220AB | | | | NTD560 NTB601 | | NTD1210 (MP-80) NTB897 (MP-80) | 2SD1296 (MP-80) NTD412 (TO-3) | 2SD1297 (MP-80) |
| 400 | TO-220AB | | | | NTD987 NTD1162 (300V) | | NTD565 (TO-3) 2SD1298 (MP-80) | | |

59C D

Power Transistors

| V _{CEO} [V] | Package | 1.5 | 2.0 | 3.0 | 5.0 | 7.0 | 10 | 15 |
|----------------------|----------|--------------------|--------------------|--------------------------------------|----------------------|--------------------|--------------------|---------|
| 30~45 | TO-126 | | • | 2SB772 2SD882 2SB744 2SD794 | | | | |
| | TO-220AB | | | | | | NTA1129 NTC2654 | |
| | TO-126 | | | 2SB744A 2SD794A | | | | |
| 60 | TO-220AB | | | | NTA1069 NTC2516 | NTB707 NTD568 | NTD1070 (MP-80) | |
| 80 | TO-220AB | | | 2SB703 2SD743 | NTA1069A NTC2516A | NTB708 NTD569 | | |
| | TO-220AB | | NTA1008 NTC2331 | | NTC2517 | NTA1010 NTC2334 | | |
| 100~150 | MP-80 | | | | | | | NTC2750 |
| | TO-220AB | 2SA1006 2SC2336 | | | | | | |
| 400 | TO-220AB | | NTC2333 | | | NTC2335 | | |
| 400 | MP-80 | | | | | | NTC2749 | NTC2751 |

• Small-Signal Transistors

| | [mA] Package | 100 | 200 | 300 | 500 | 700~1000 |
|----------|-----------------|------------------------------------|----------------|------------------|------------------|------------------------------------|
| 25 30 | TO-92 | | | *2SC1280A | | 2SC2001, 2SA952 |
| 40 | TO-92 TO-18 | | 2SC943, 2SA603 | | 2SC2720, 2SA1153 | |
| 50 | TO-92 SP-8 | 2SC945, 2SA733 2SC2718, 2SA1151 | | | | 00DE74_00D60E |
| 60 | TO-92 SP-8 | | | 2SC2003, 2SA954 | | 2SD571, 2SB605 2SC2721, 2SA1154 |
| 80 | TO-92 SP-8 | | | 2SC2719, 2SA1152 | | 2SD1312, 2SB984 |

• Mini-Mold Transistors for Hybrid ICs

| Type No. | Ic [mA] | V _{CEO} [V] | Pd [mW] |
|----------|---------|----------------------|---------|
| 2SA811A | -50 | -120 | 200 |
| 2SA812 | -100 | -50 | 150 |
| 2SB624 | -700 | -25 | 200 |
| 2SB736 | -300 | -60 | 200 |
| 2SC1622A | 50 | 120 | 200 |
| 2SC1623 | 100 | 50 | 150 |
| 2SC1654 | 50 | 160 | 150 |
| 2SD596 | 700 | 25 | 200 |
| 2SD780 | 300 | 60 | 200 |

• Power Mini-Mold Transistors for Hybrid ICs

| NPN No. | V _{CEO} [V] | Ic [A] | P _T [W] | h _{FE} [—] | PNP No. |
|---------|----------------------|--------|--------------------|---------------------|---------|
| 2SD1000 | 50 | 0.7 | 2.0 | 90~400 | 2SB799 |
| 2SD1006 | 100 | 0.7 | 2.0 | 90~400 | 2SB805 |
| 2SD1007 | 120 | 0.7 | 2.0 | 90~400 | 2SB806 |
| 2SD999 | 25 | 1.0 | 2.0 | 90~400 | 2SB798 |
| 2SD1005 | 80 | 1.0 | 2.0 | 90~400 | 2SB804 |
| 2SD1001 | 50 | 0.3 | 2.0 | 90~400 | 2SB800 |
| | | | | • | |

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www.datasheetcatalog.com

Datasheets for electronics components.